FAIRCHILD

SEMICONDUCTOR®

KSC1983

High Gain Power Transistor



1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

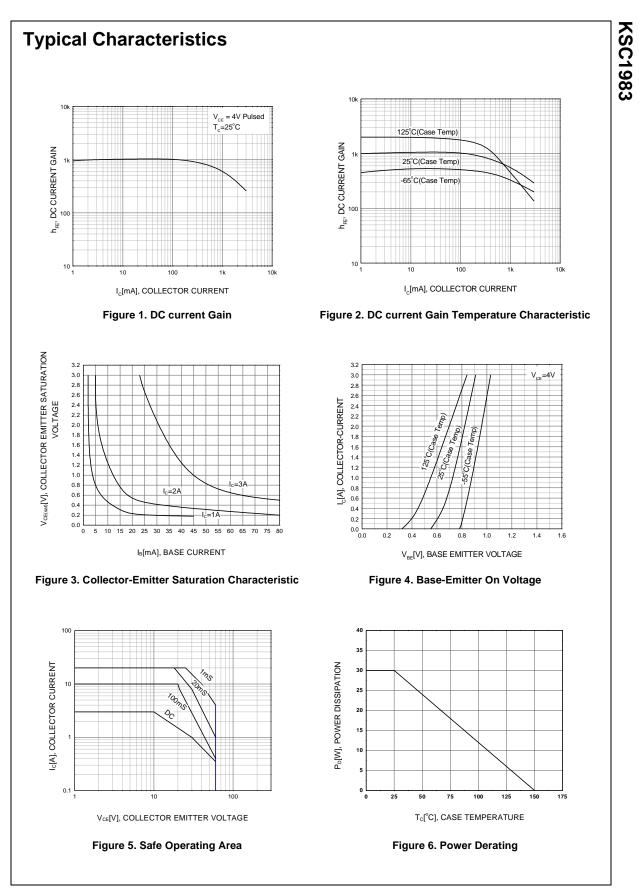
Absolute Maximum Ratings $T_{C}=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	80	V	
V _{CEO}	Collector-Emitter Voltage	60	V	
V _{EBO}	Emitter-Base Voltage	6	V	
I _C	Collector Current	3	А	
I _B	Base Current	1	А	
P _C	Collector Dissipation (T _C =25°C)	30	W	
TJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 55 ~ 150	°C	

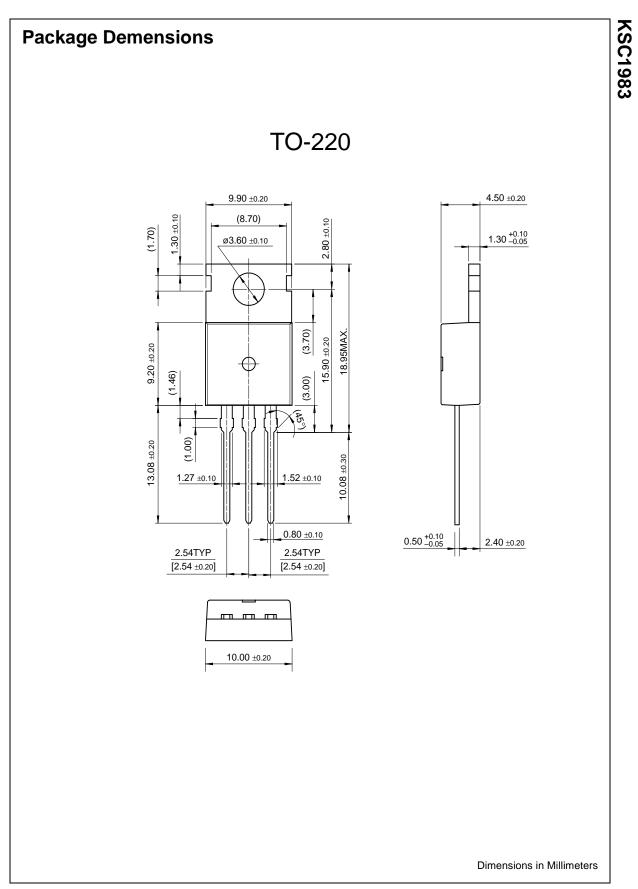
Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I _{CBO}	Collector Cut-off Current	$V_{CB} = 80V, I_E = 0$			100	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 6V, I_{C} = 0$			100	μΑ
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 25 {\rm mA}, I_{\rm B} = 0$	60			V
h _{FE}	* DC Current Gain	$V_{CE} = 4V, I_{C} = 0.5A$	500			
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	$I_{\rm C} = 2A, I_{\rm B} = 0.05A$			1	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 12V, I_{C} = 0.2A$		15		MHz

* Pulse Test: PW≤350µs, Duty Cycle≤2% Pulsed



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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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